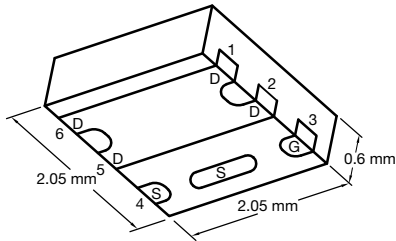




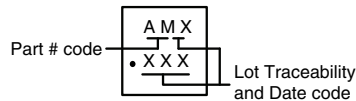
N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
30	0.017 at $V_{GS} = 10$ V	12	5 nC
	0.022 at $V_{GS} = 4.5$ V	12	

Thin PowerPAK SC-70-6L-Single



Marking Code



Ordering Information:

SiA444DJT-T1-GE3 (Lead (Pb)-free and Halogen-free)

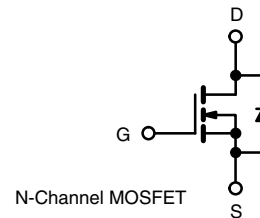
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- New Thermally Enhanced PowerPAK[®] SC-70 Package
 - Small Footprint Area
 - Ultra-Thin 0.6 mm height
- Compliant to RoHS Directive 2002/95/EC


RoHS
 COMPLIANT
 HALOGEN
FREE

APPLICATIONS

- DC/DC Converter
- High Frequency Switching



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C	12 ^a
		$T_C = 70$ °C	12 ^a
		$T_A = 25$ °C	11 ^{a, b, c}
		$T_A = 70$ °C	8.8 ^{b, c}
Pulsed Drain Current ($t = 300$ μ s)	I_{DM}	40	A
Continuous Source-Drain Diode Current	I_S	$T_C = 25$ °C	
		$T_A = 25$ °C	2.9 ^{b, c}
Maximum Power Dissipation	P_D	$T_C = 25$ °C	19
		$T_C = 70$ °C	12
		$T_A = 25$ °C	3.5 ^{b, c}
		$T_A = 70$ °C	2.2 ^{b, c}
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	R_{thJA}	28	36	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	5.3	6.5	

Notes:

- Package limited
- Surface mounted on 1" x 1" FR4 board.
- $t = 5$ s.
- See solder profile (www.vishay.com/ppg?73257). The Thin PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 80 °C/W.



SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		34		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 4.8		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1		2.2	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	20			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 7.4\text{ A}$		0.014	0.017	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 6.5\text{ A}$		0.017	0.022	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 10\text{ V}, I_D = 7.4\text{ A}$		24		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		560		pF
Output Capacitance	C_{oss}			125		
Reverse Transfer Capacitance	C_{rss}			55		
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 11\text{ A}$		10	15	nC
		$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 11\text{ A}$		5	8	
Gate-Source Charge	Q_{gs}			1.5		
Gate-Drain Charge	Q_{gd}		1.7			
Gate Resistance	R_g	$f = 1\text{ MHz}$	0.7	3.5	7	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 1.7\text{ }\Omega$ $I_D \cong 8.8\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		12	20	ns
Rise Time	t_r			12	20	
Turn-Off Delay Time	$t_{d(off)}$			15	25	
Fall Time	t_f			10	15	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 1.7\text{ }\Omega$ $I_D \cong 8.8\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		7	15	
Rise Time	t_r			12	20	
Turn-Off Delay Time	$t_{d(off)}$			15	25	
Fall Time	t_f			10	15	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			12	A
Pulse Diode Forward Current	I_{SM}				40	
Body Diode Voltage	V_{SD}	$I_S = 8.8\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 8.8\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		15	30	ns
Body Diode Reverse Recovery Charge	Q_{rr}			6	12	nC
Reverse Recovery Fall Time	t_a			7.5		ns
Reverse Recovery Rise Time	t_b			7.5		

Notes:

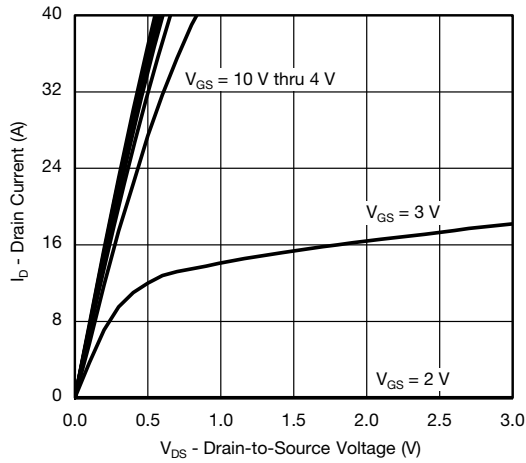
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

b. Guaranteed by design, not subject to production testing.

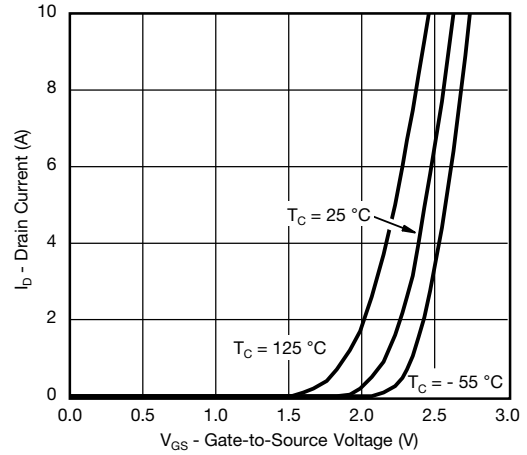
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



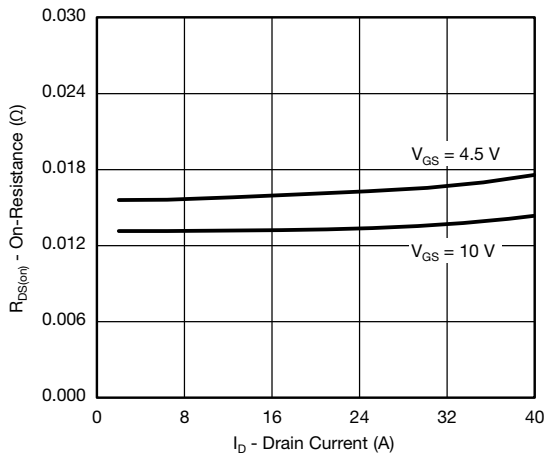
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



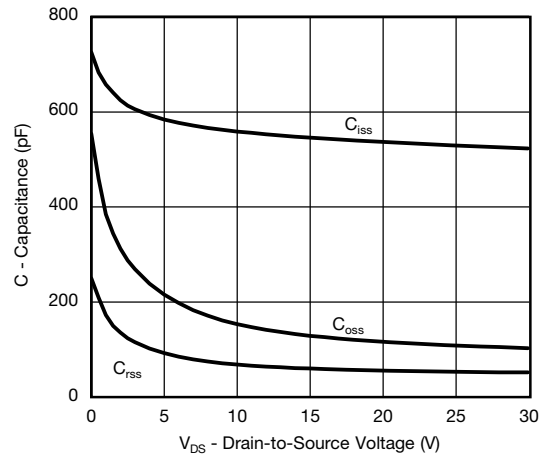
Output Characteristics



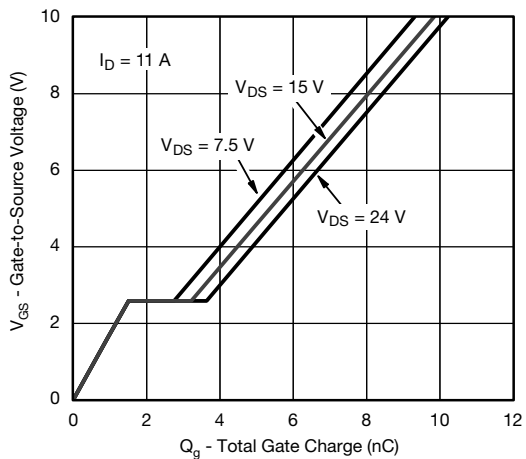
Transfer Characteristics



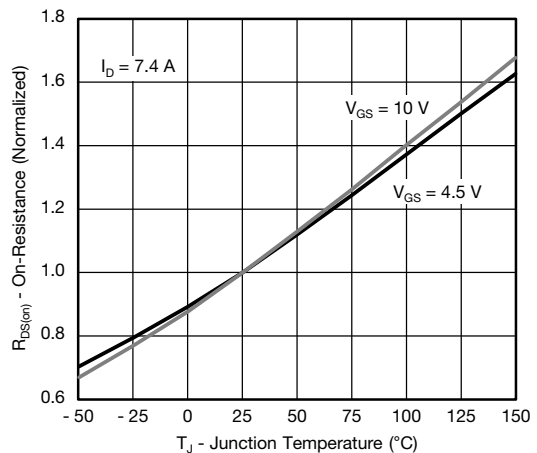
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



Gate Charge



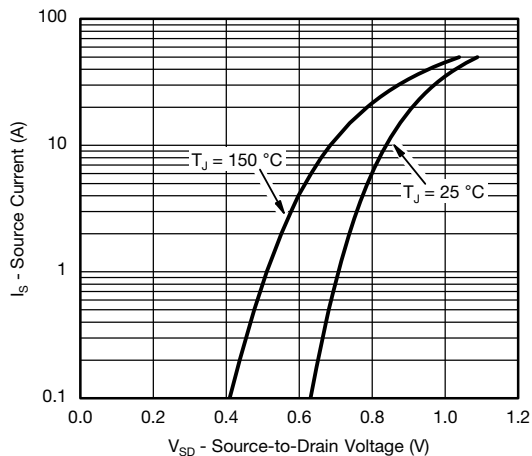
On-Resistance vs. Junction Temperature

SiA444DJT

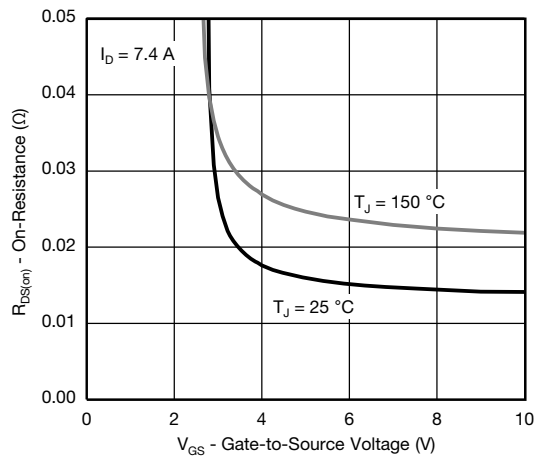
Vishay Siliconix



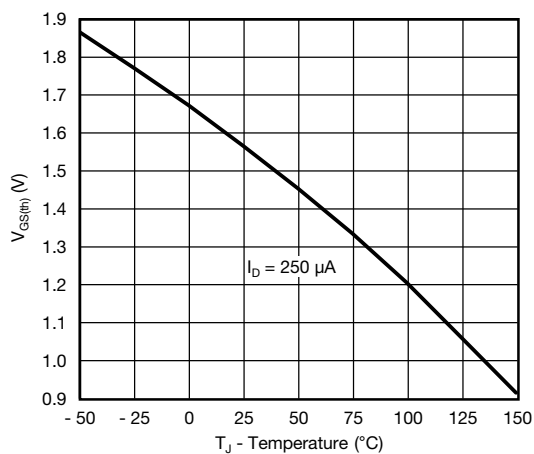
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



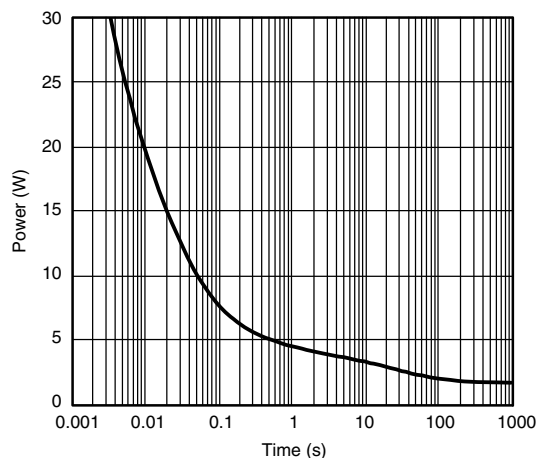
Source-Drain Diode Forward Voltage



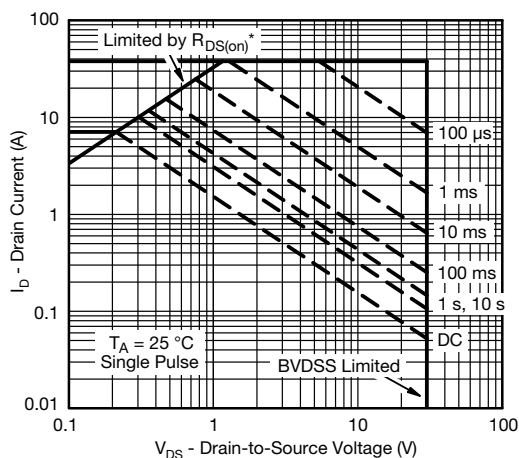
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



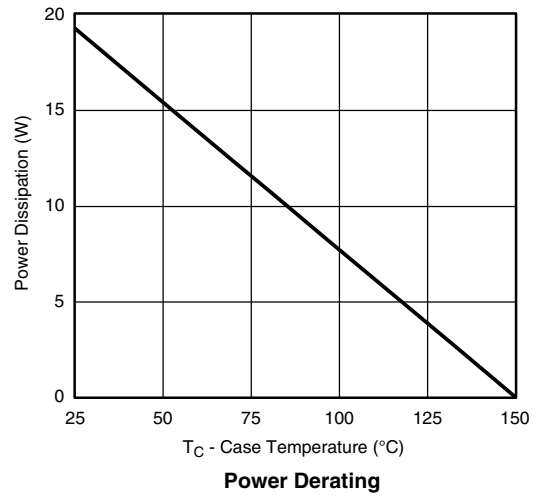
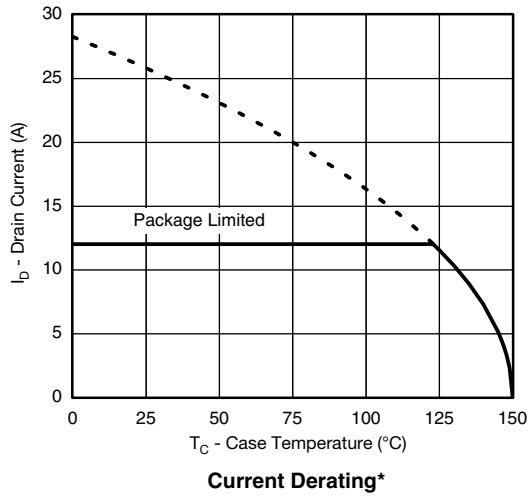
Single Pulse Power (Junction-to-Ambient)



Safe Operating Area, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



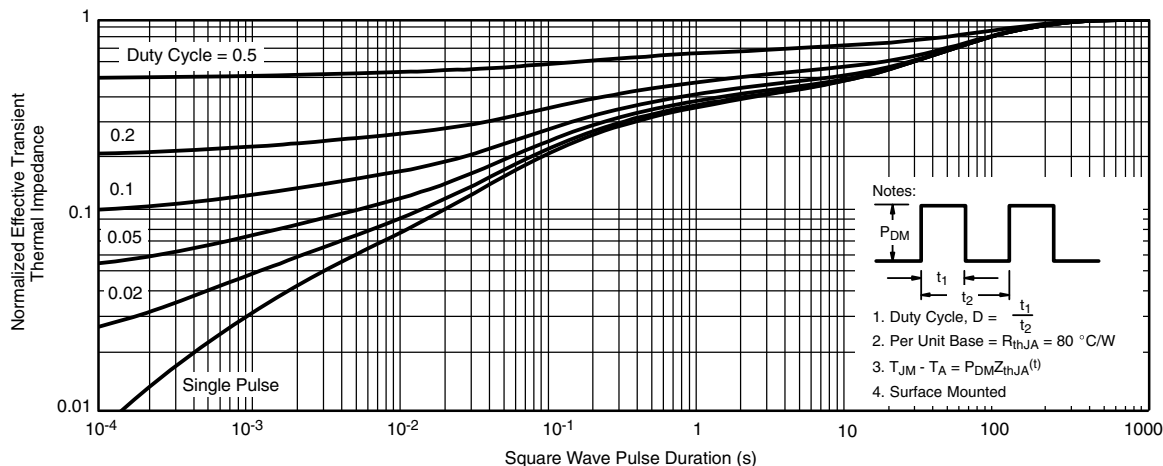
* The power dissipation P_D is based on $T_{J(max)} = 150\text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

SiA444DJT

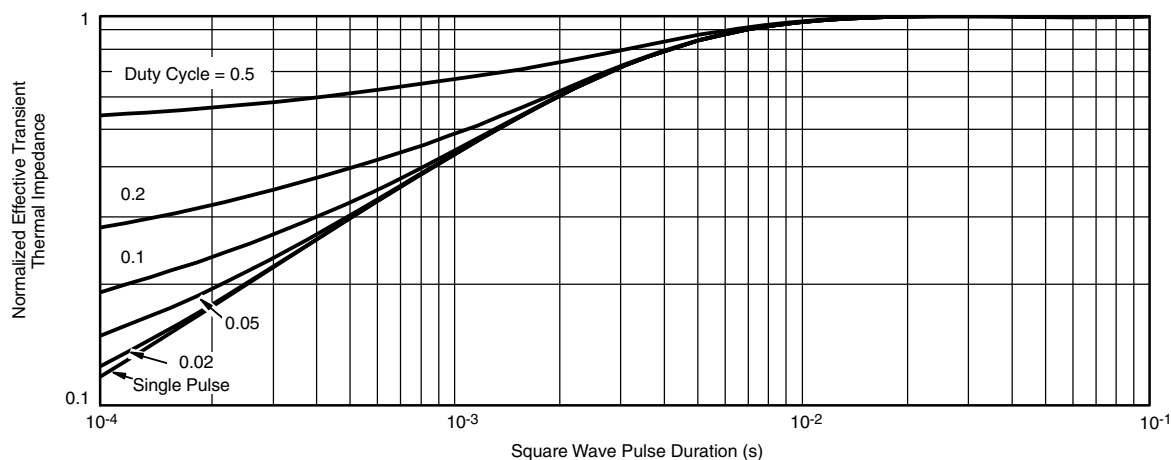
Vishay Siliconix



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



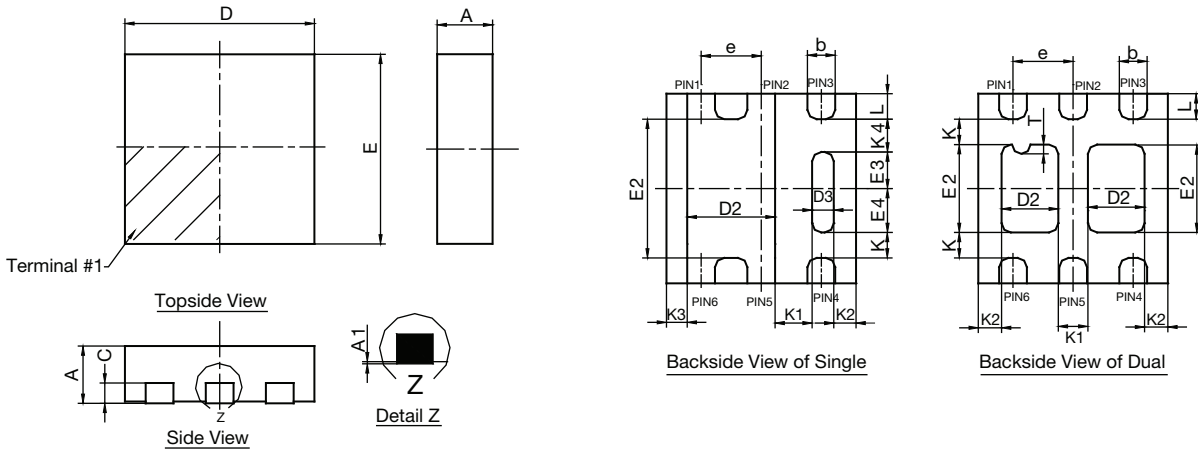
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67056.

Case Outline for PowerPAK® SC70T



DIM.	SINGLE PAD						DUAL PAD					
	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.525	0.60	0.65	0.0206	0.024	0.026	0.525	0.60	0.65	0.0206	0.024	0.026
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
C	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D2	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D3	0.135	0.235	0.335	0.005	0.009	0.013						
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E2	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E3	0.345	0.395	0.445	0.014	0.016	0.018						
E4	0.425	0.475	0.525	0.017	0.019	0.021						
e	0.65 BSC			0.026 BSC			0.65 BSC			0.026 BSC		
K	0.275 TYP.			0.011 TYP.			0.275 TYP.			0.011 TYP.		
K1	0.400 TYP.			0.016 TYP.			0.320 TYP.			0.013 TYP.		
K2	0.240 TYP.			0.009 TYP.			0.252 TYP.			0.010 TYP.		
K3	0.225 TYP.			0.009 TYP.								
K4	0.355 TYP.			0.014 TYP.								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
T							0.05	0.10	0.15	0.002	0.004	0.006
ECN: C12-0160-Rev. B, 05-Mar-12 DWG: 5994												

Notes

1. All dimensions are in millimeter. Millimeters will govern.
2. Package outline exclusive of mold flash and metal burr.
3. Package outline inclusive of plating



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